

Silicon PNP Darlington Power Transistor

BDX88/A/B/C

DESCRIPTION

- High DC Current Gain-
 : $h_{FE} = 750(\text{Min}) @ I_C = -6\text{A}$
- Collector-Emitter Sustaining Voltage-
 : $V_{CE0(\text{SUS})} = -45\text{V}(\text{Min})$ - BDX88; $-60\text{V}(\text{Min})$ - BDX88A
 $-80\text{V}(\text{Min})$ - BDX88B; $-100\text{V}(\text{Min})$ - BDX88C
- Complement to Type BDX87/A/B/C

APPLICATIONS

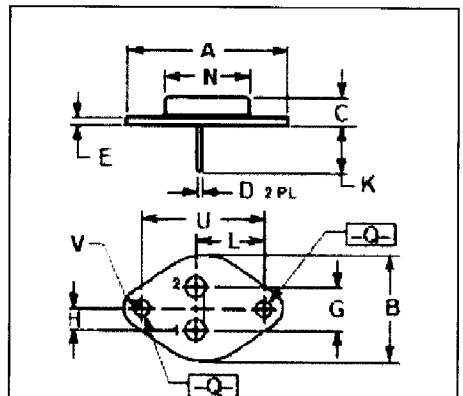
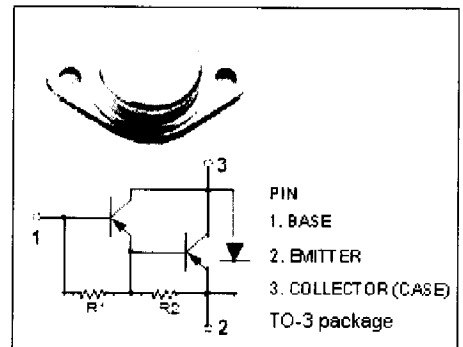
- Designed for use in power linear and switching applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

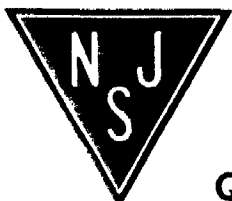
SYMBOL	PARAMETER	VALUE	UNIT
V_{CB0}	Collector-Base Voltage	BDX88	-45
		BDX88A	-60
		BDX88B	-80
		BDX88C	-100
V_{CE0}	Collector-Emitter Voltage	BDX88	-45
		BDX88A	-60
		BDX88B	-80
		BDX88C	-100
V_{EB0}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-12	A
I_{CM}	Collector Current-Peak	-18	A
I_B	Base Current	-200	mA
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	120	W
T_J	Junction Temperature	200	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R_{th-j-c}	Thermal Resistance, Junction to Case	1.45	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
M	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50



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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	BDX88	$I_C = -100\text{mA}; I_B = 0$			V
		BDX88A		-45		
		BDX88B		-60		
		BDX88C		-80		
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -6\text{A}; I_B = -24\text{mA}$			-2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -12\text{A}; I_B = -120\text{mA}$			-3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -12\text{A}; I_B = -120\text{mA}$			-4.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -6\text{A}; V_{CE} = -3\text{V}$			-2.8	V
I_{CBO}	Collector Cutoff Current	BDX88	$V_{CB} = -45\text{V}; I_E = 0$ $V_{CB} = -45\text{V}; I_E = 0; T_C = 150^\circ\text{C}$			mA
		BDX88A		-0.5		
		BDX88B		-5.0		
		BDX88C		-0.5		
I_{CEO}	Collector Cutoff Current	BDX88	$V_{CE} = -22\text{V}; I_B = 0$			mA
		BDX88A		-1.0		
		BDX88B		-1.0		
		BDX88C		-1.0		
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-2.0	mA
h_{FE-1}	DC Current Gain	$I_C = -5\text{A}; V_{CE} = -3\text{V}$	1000			
h_{FE-2}	DC Current Gain	$I_C = -6\text{A}; V_{CE} = -3\text{V}$	750		18000	
h_{FE-3}	DC Current Gain	$I_C = -12\text{A}; V_{CE} = -3\text{V}$	100			